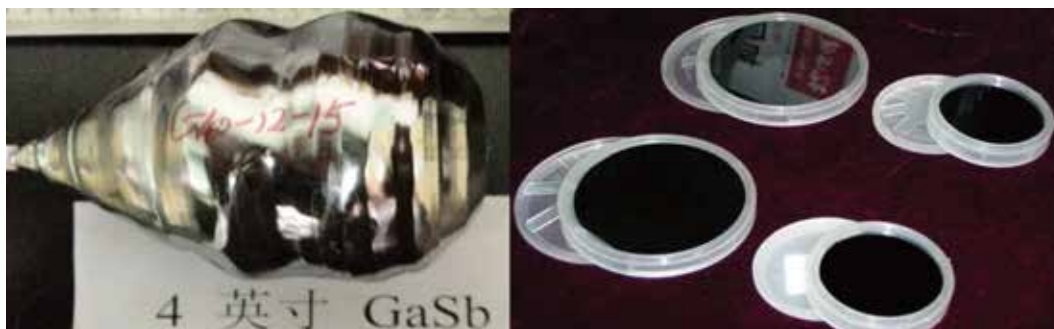


# GaSb-Gallium Antimonide



Electrical and Dopant Specifications				
Dopant	Type	Carrier concentration (cm <sup>-3</sup> )	Mobility (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )	E.P.D (cm <sup>-2</sup> )
Undoped	p-type	(1-2)x10 <sup>17</sup>	600-700	≤3000
Zn-InP	p-type	(5-100)x10 <sup>17</sup>	200-500	≤3000
Te-InP	P-type	(1-20)x10 <sup>17</sup>	2000-3500	≤3000
GaSb Wafer Specifications				
Size	2"	3"	4"	
Diameter(mm)	50.5±0.5	76.2±0.5	100.0±0.5	
Thickness(um)	500±25	600±25	800±25	
Orientation	(100)/(111) ±0.5°			
Major Flat Length(mm)	16±2	22±2	32.5±2	
Minor Flat length(mm)	8±1	11±1	18±1	
TTV(um)	<10	<10	<15	
Bow(um)	<10	<10	<15	
Warp(um)	<15	<15	<15	